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107548203

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL. KUMONI

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U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TWP		5,221,413	06/22/93	Brasen, et al.	117	89	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
TWP	JPA	2003-78118	03/14/03	Japan			Abstract
	JPA	2003-78140	03/14/03	Japan			Abstract
	JPA	2003-178977	06/27/03	Japan			Abstract
	JPA	2003-282464	10/03/03	Japan			Abstract
	JPA	2003-282463	10/03/03	Japan			Abstract
	JPA	2004-342975	12/02/04	Japan			Abstract
	JPA	11-195562	07/21/99	Japan			Abstract
↓	JPA	07-302889	11/14/95	Japan			Abstract
TWP	EP	1248294 A2	10/09/02	EPO			

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

TWP		Current, I, Michael., et al. "Atomic-Layer Cleaving with Si,Ge, Strain Layers For Fabrication of Si and Ge-rich SOI Device Layers" IEEE International SOI Conference, October 1, 2001, pp. 11-12.
		Shin-ichi Takagi, "Metal-Oxide-Semiconductor (MOS) device technologies using Si/Ge heretointerfaces", Oyo Buturi, Vol. 72, NO. 3, pp. 284-290, 2003.
		T.A. Langdo, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 4256-4258 (2003).
		D.J. Godbey, et al., Appl. Phys. Lett., vol. 56, no. 4, pp. 373-379 (1990).
↓		D. Ferijoo, et al., J. Electro. Mat., vol. 23, no. 6, pp. 493-496 (1994).
TWP		A.H. Krist, et al., Appl. Phys. Lett., vol. 58, no. 17, pp. 1899-1901 (1991).

EXAMINER

DATE CONSIDERED

05/18/2005

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.